

IN THE CLAIMS

Please amend the claims as follows. This listing of claims will replace all prior versions, and listings, of claims in the application.

1. (currently amended) An apparatus product suitable for simulating a standard wafer in semiconductor manufacturing equipment, comprising:

a support first layer composed of a material suitable for being handled by the semiconductor manufacturing equipment; and

a second layer composed of a mixture of multiple materials disposed entirely over the first layer mixture including a process agent and a material, the mixture of the multiple materials configured to simultaneously generate byproducts during an etching operation being applied to the support layer, wherein the byproducts are similar to byproducts produced by the standard wafer apparatus simulates a wafer including the material and having the process agent thereon.

2. (currently amended) The apparatus product of claim 1, wherein the multiple materials include a photoresist and a metal process agent is photoresist.

3. (currently amended) The apparatus product of claim 1, wherein the multiple materials include both a polymer and a material selected from the group consisting of is silicon and the apparatus simulates a wafer including polysilicon silicon, tungsten, tungsten silicide, titanium, titanium nitride, silicon dioxide, aluminum, platinum, ruthenium, ruthenium oxide, copper, tantalum, and nickel.

Claims 4-15 (canceled)

16. (currently amended) The apparatus product of claim 1, wherein the mixture of multiple materials includes three or more materials ~~support layer is at least one of a disc and a wafer.~~

17. (currently amended) The apparatus product of claim 1, wherein the second layer is capable of withstanding cumulative etching time of up to 120 radio frequency minutes ~~support layer includes at least one of silicon, metal, plastic, and an oxide.~~

18. (currently amended) The apparatus product of claim 1, wherein the mixture of the multiple materials and the process agent of the mixture are baked on the support first layer.

19. (currently amended) The apparatus of claim 1, wherein a ratio of the multiple materials in the mixture ~~between the material to the process agent~~ corresponds to an exposed area on the standard wafer ~~to be being~~ simulated.